具有三态输出的双路总线缓冲器闸

查询样片: SN74LVC2G126-EP

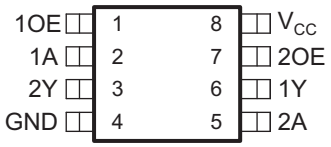
特性

- 支持 **5V V_{CC}** 运行
- 输入接受的电压达到高达 **5.5V**
- 电压为 **3.3V** 时，**t_{pd}** 最大值为 **6.8ns**
- 低功耗，最大 **I_{CC}** 为 **10μA**
- 电压为 **3.3V** 时，输出驱动为 **±24mA**
- **V_{CC} = 3.3V，T_A = 25°C** 时，**V_{OLP}**（输出地弹反射）
  典型值小于 **0.8V**。
- **V_{CC} = 3.3V，T_A = 25°C** 时，**V_{OHV}**（输出 **V_{OH}** 下冲）
  典型值大于 **2V**。
- **I_{off}** 支持部分断电模式工作
- 锁断性能超过 **100mA**（符合 **JESD 78，II** 类规范的要求）
- 静电放电 **(ESD)** 保护性能超过 **JESD 22** 规范要求
  - **2000V** 人体模型 **(A114-A)**
  - **200V** 机器模型 **(A115-A)**
  - **1000V** 充电器件模型 **(C101)**

支持国防、航空航天、和医疗应用

- 受控基线
- 同一组装和测试场所
- 一个制造场所
- 支持军用（**-55°C** 至 **125°C**）温度范围
- 延长的产品生命周期
- 延长的产品变更通知
- 产品可追溯性

DCU 封装
（顶视图）



说明

这款双路总线缓冲器闸被设计用于 1.65V 至 5.5V V_{CC} 运行。

SN74LVC2G126 是一款具有三态输出的双路总线驱动器/线路驱动器。 当相关输出使能 (OE) 输入为低电平时，输出被禁用。

为了确保加电或断电期间的高阻抗状态，OE 应该通过一个下拉电阻器接在接地 (GND) 上；此电阻器的最小值由驱动器的电流供源能力决定。

该器件完全符合使用 I_{off} 的部分断电应用的规范要求。 I_{off} 电路禁用输出，从而可防止其断电时破坏性电流从该器件回流。

ORDERING INFORMATION(1)

T_J	PACKAGE(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING	VID NUMBER
–55°C to 125°C	VSSOP - DCU	Tape of 250	CLVC2G126MDCUTEP	CEPR	V62/14604-01XE

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
(2) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

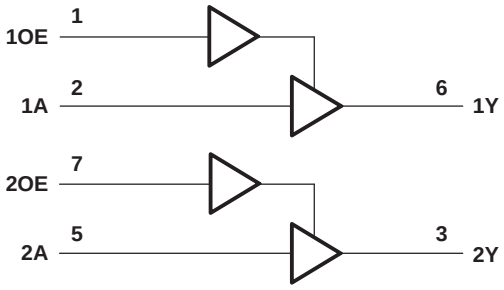
Function Table
(Each Buffer)

INPUTS		OUTPUT
OE	A	Y
H	H	H

Function Table
(Each Buffer) (continued)

INPUTS		OUTPUT
OE	A	Y
H	L	L
L	X	Z

Logic Diagram (Positive Logic)



ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	6.5	V
V_I	Input voltage range(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state(2) (3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_J	Absolute maximum junction temperature range		–55	150	°C
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(3) The value of V_{CC} is provided in the recommended operating conditions table.

THERMAL INFORMATION

THERMAL METRIC(1)		SN74LVC2G126-EP	UNITS
		DCU	
		8 PINS	
θ_{JA}	Junction-to-ambient thermal resistance(2)	204.3	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance(3)	78	
θ_{JB}	Junction-to-board thermal resistance(4)	83	
ψ_{JT}	Junction-to-top characterization parameter(5)	7.6	
ψ_{JB}	Junction-to-board characterization parameter(6)	82.6	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance(7)	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
(5) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
(6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).
(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

RECOMMENDED OPERATING CONDITIONS(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 3 V to 3.6 V	2		
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 3 V to 3.6 V		0.8	
		V_{CC} = 4.5 V to 5.5 V		0.3 × V_{CC}	
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3-state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–8	
		V_{CC} = 3 V		–16	
				–24	
		V_{CC} = 4.5 V		–32	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		8	
		V_{CC} = 3 V		16	
				24	
		V_{CC} = 4.5 V		32	
Δt/Δv	Input transition rise or fall rate	V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V_{CC} = 3.3 V ± 0.3 V		10	
		V_{CC} = 5 V ± 0.5 V		5	
T_J	Operating virtual junction temperature		–55	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS

These specifications apply for –55°C ≤ T_J ≤ 125°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP(1)	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		1.65 V to 5.5 V	V_{CC} – 0.1			V
		I_{OH} = –4 mA		1.65 V	1.2			
		I_{OH} = –8 mA		2.3 V	1.9			
		I_{OH} = –16 mA		3 V	2.4			
		I_{OH} = –24 mA			2.3			
		I_{OH} = –32 mA		4.5 V	3.8			
V_{OL}		I_{OL} = 100 µA		1.65 V to 5.5 V			0.1	V
		I_{OL} = 4 mA		1.65 V			0.45	
		I_{OL} = 8 mA		2.3 V			0.3	
		I_{OL} = 16 mA		3 V			0.4	
		I_{OL} = 24 mA					0.55	
		I_{OL} = 32 mA		4.5 V			0.55	
I_I	A or OE inputs	V_I = 5.5 V or GND		0 to 5.5 V			±5	µA
I_{off}		V_I or V_O = 5.5 V		0			±10	µA
I_{OZ}		V_O = 0 to 5.5 V		3.6 V			10	µA
I_{CC}		V_I = 5.5 V or GND,	I_O = 0	1.65 V to 5.5 V			10	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 5.5 V			500	µA
C_I	Data inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Control inputs					4		
C_o		V_O = V_{CC} or GND		3.3 V		6.5		pF

(1) All typical values are at V_{CC} = 3.3 V, T_J = 25°C.

SWITCHING CHARACTERISTICS

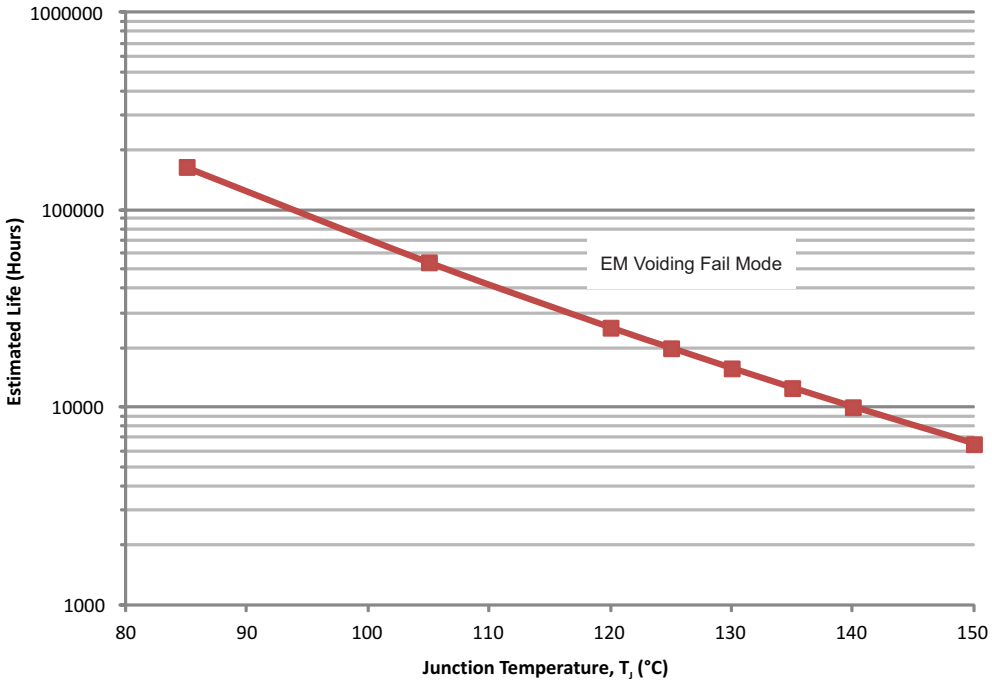
These specifications apply for –55°C ≤ T_J ≤ 125°C (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	3.5	15.2	1.7	8.6	1.4	6.8	1	5.5	ns
t_{en}	OE	Y	3.5	15.2	1.7	8.6	1.5	6.8	1	5.5	ns
t_{dis}	OE	Y	1.7	12.6	1	5.7	1	4.5	0.1	3.3	ns

OPERATING CHARACTERISTICS

T_J = 25°

PARAMETER			TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	V_{CC} = 5 V	UNIT
				TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	f = 10 MHz	19	19	20	22	pF
		Outputs disabled		2	2	2	3	



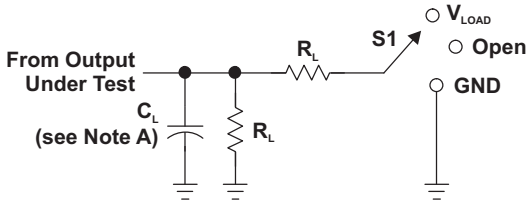
(1) See datasheet for absolute maximum and minimum recommended operating conditions.

(2) Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).

(3) Enhanced plastic product disclaimer applies.

Figure 1. SN74LVC2G126-EP Operating Life Derating Chart

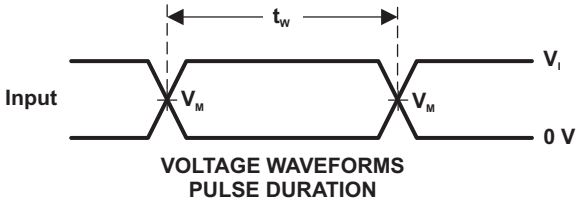
PARAMETER MEASUREMENT INFORMATION



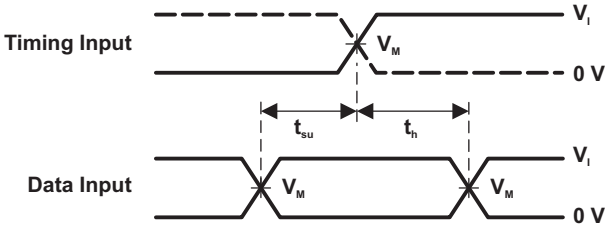
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

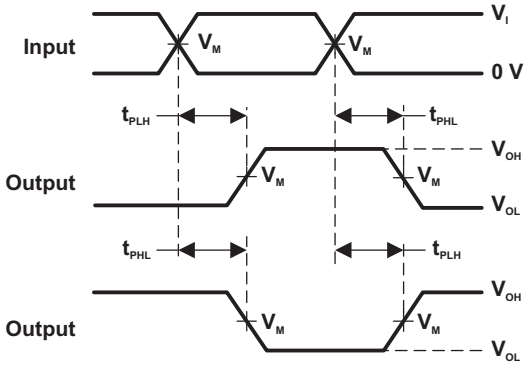
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	50 pF	500 Ω	0.3 V



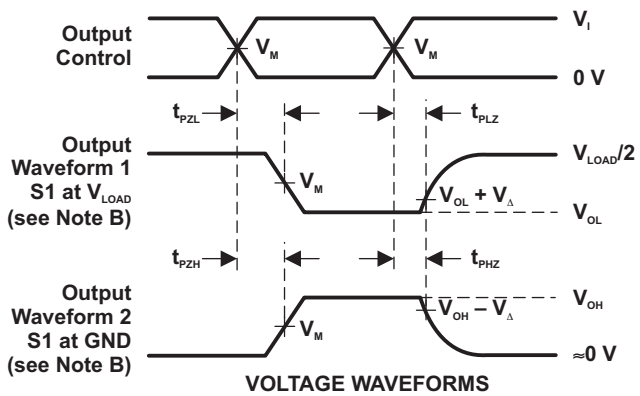
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CLVC2G126MDCUTEP	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CEPR	Samples
V62/14604-01XE	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CEPR	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

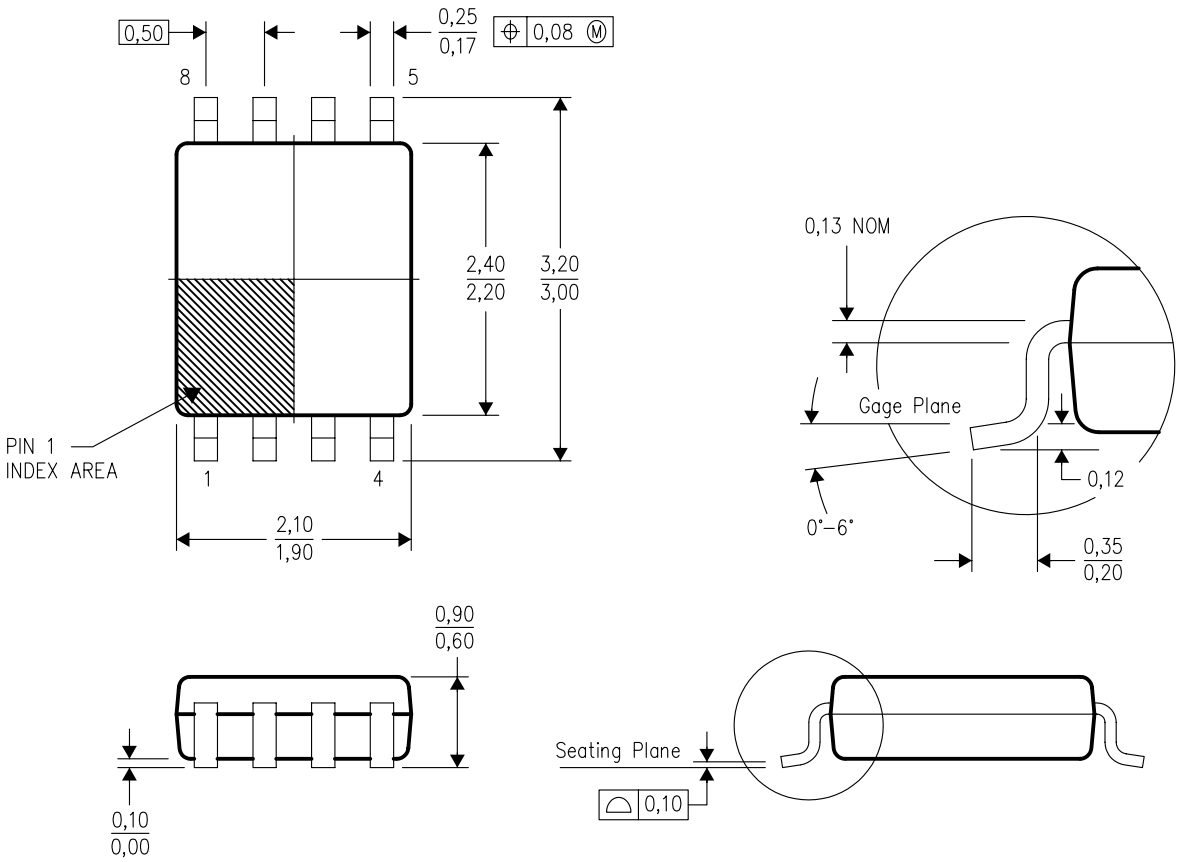
(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

DCU (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE (DIE DOWN)



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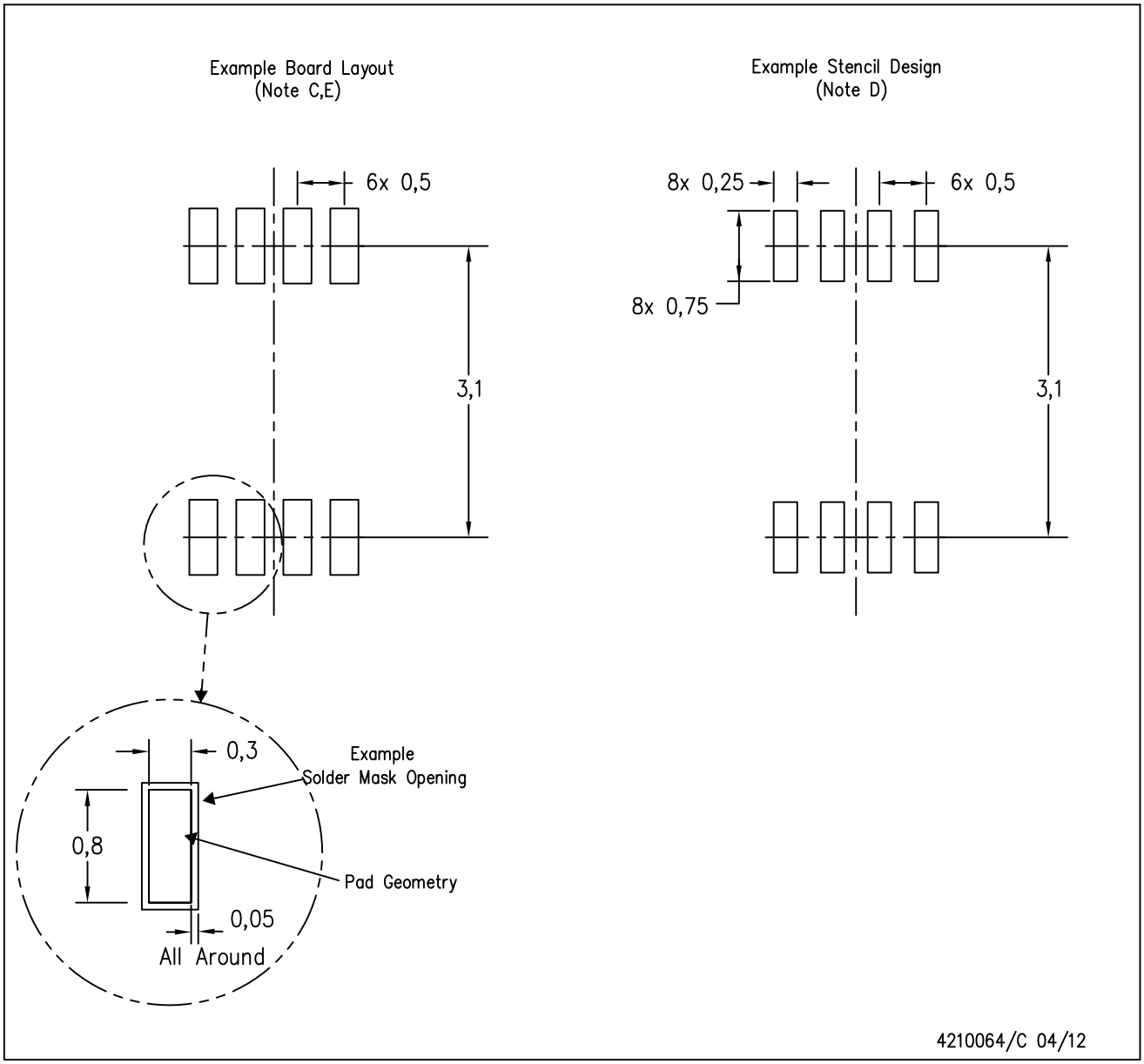
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–187 variation CA.

DCU (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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